

Symbol		Test Conditions	Charac	teristic Va	alues
$(T_{J} = 25^{\circ})$	°C, L	Inless Otherwise Specified)	Min.	Тур.	Max.
g _{fs}		$I_{\rm C} = I_{\rm C100}, V_{\rm CE} = 10V, \text{ Note 1}$	10	17	S
C _{ies})			1790	pF
C _{oes}	}	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		145	pF
C _{res}	J			50	pF
$\overline{\mathbf{Q}_{g}}$)			88	nC
\mathbf{Q}_{ge}	}	$I_{\rm C} = I_{\rm C100}, V_{\rm GE} = 15 \rm V, V_{\rm CE} = 0.5 \bullet \rm V_{\rm CES}$		18	nC
Q _{gc}	J			30	nC
t _{d(on)}	١			19	ns
t _{ri}		Inductive load, T _J = 25°C		12	ns
E _{on}		$I_{\rm C} = I_{\rm C100}, V_{\rm GE} = 15V$		1.35	mJ
$\mathbf{t}_{d(off)}$	($V_{CE} = 0.5 \cdot V_{CES}, R_G = 5\Omega$		110	ns
t _{fi}		Note 2		32	ns
E_{off}	J	Note 2		0.44	0.80 mJ
t _{d(on)})			22	ns
t _{ri}		Inductive load, T _J = 125°C		13	ns
E _{on}	($I_C = I_{C100}, V_{GE} = 15V$		2.33	mJ
$\mathbf{t}_{d(off)}$		$V_{CF} = 0.5 \cdot V_{CFS}, R_G = 5\Omega$		144	ns
t _{fi}		Note 2		380	ns
E _{off}	<i>J</i>			1.64	mJ
R _{thJC}					0.50 °C/W
R _{thCK}		TO-247		0.21	°C/W

Terminals: 1 - Gate 2 - Collector 3 - Emitter

Dim.	Millimeter		Inches		
	Min.	Max.	Min.	Max.	
Α	4.7	5.3	.185	.209	
A ₁	2.2	2.54	.087	.102	
A ₂	2.2	2.6	.059	.098	
b	1.0	1.4	.040	.055	
b,	1.65	2.13	.065	.084	
b	2.87	3.12	.113	.123	
С	.4	.8	.016	.031	
D	20.80	21.46	.819	.845	
Е	15.75	16.26	.610	.640	
е	5.20	5.72	0.205	0.225	
L	19.81	20.32	.780	.800	
L1		4.50		.177	
ØP	3.55	3.65	.140	.144	
Q	5.89	6.40	0.232	0.252	
R	4.32	5.49	.170	.216	
S	6.15	BSC	242	BSC	

Reverse Diode (FRED)

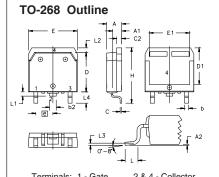
Symbol $(T_J = 2)$	ol Test Conditions C 5°C, Unless Otherwise Specified) Mi	haracteristic n. Typ.	Values Max.
V _F	$I_F = 20A$, $V_{GE} = 0V$, Note 1 $T_A = 125$ °C	2.8	3.0 V
I _{RM}	$I_{E} = 20A, V_{CE} = 0V,$	19	A
t _{rr}	$\int_{e}^{4\pi} -di_{F}/dt = 750A/\mu s, V_{R} = 800V$	70	ns
R _{thJC}			0.9 °C/W

Notes:

- 1. Pulse test, $t \le 300\mu s$, duty cycle, $d \le 2\%$.
- 2. Switching times & energy losses may increase for higher $V_{CE}(Clamp)$, T_{J} or R_{G} .

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.



Terminals: 1 - Gate 2 & 4 - Collector 3 - Emitter

MYZ	INCHES		MILLIMETERS		
2114	MIN	MAX	MIN	MAX	
Α	.193	.201	4.90	5.10	
A1	.106	.114	2.70	2.90	
A2	.001	.010	0.02	0.25	
b	.045	.057	1.15	1.45	
b2	.075	.083	1.90	2.10	
С	.016	.026	0.40	0.65	
C2	.057	.063	1.45	1.60	
D	.543	.551	13.80	14.00	
D1	.488	.500	12.40	12.70	
Е	.624	.632	15.85	16.05	
E1	.524	.535	13.30	13.60	
е	.215	BSC	5.45 BSC		
Н	.736	.752	18.70	19.10	
٦	.094	.106	2.40	2.70	
L1	.047	.055	1.20	1.40	
L2	.039	.045	1.00	1.15	
L3	.010	0 BSC 0.25 BSC			
L4	.150	.161	3.80	4.10	

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5.049.961 5.237.481 6.162.665 6,404,065 B1 6.683.344 6,727,585 7,005,734 B2 7,157,338B2 by one or more of the following U.S. patents: 4,850,072 5,063,307 5,381,025 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2 5,017,508 6,259,123 B1 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,771,478 B2 7,071,537



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